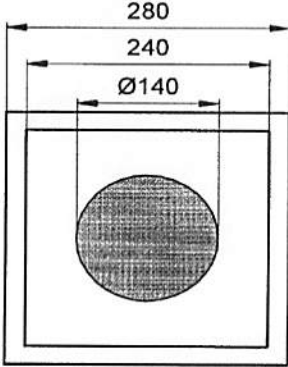


| Radiation | Type | Electrodes |
|-----------|----------------------|----------------|
| deep red | AlGaAs / AlGaAs, DDH | N (cathode) up |

| | |
|---|---|
|  | typ. dimensions (μm) |
| | typ. thickness: 160 ± 20 μm cathode: gold alloy, thickness 1.5 μm anode: gold alloy, thickness 0.5 μm |

Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

| Parameter | Test cond. | Symbol | Min | Typ | Max | Unit |
|----------------------|---------------|-----------------------|-----|--------|-----|------|
| Forward voltage | $I_F = 20$ mA | V_F | | 1.8 | 2.3 | V |
| Reverse voltage | $I_R = 10$ μA | V_R | 5 | | | V |
| Radiant power* | $I_F = 20$ mA | Φ_e | 1.5 | 1.8 | | mW |
| Radiant power** | $I_F = 20$ mA | Φ_e | | 2.8 | | mW |
| Luminous intensity* | $I_F = 20$ mA | I_V | 35 | | | mcd |
| Luminous intensity** | $I_F = 20$ mA | I_V | | 55 | | mcd |
| Peak wavelength | $I_F = 20$ mA | λ_p | 657 | 660 | 663 | nm |
| FWHM | $I_F = 20$ mA | $\Delta\lambda_{0.5}$ | | 25 | | nm |
| Switching times | $I_F = 20$ mA | t_r, t_f | | 80; 90 | | ns |

*Measured on bare chip on TO-18 header

**Measured on epoxy-covered chip on TO-18 header

Packing

Chips on adhesive film with wire-bond side top

Art. No. 112 001



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.